SMC SANGDEST MICROELECTRONICS

FR301G-FR307G 3.0A GLASS PASSIVATED FAST RECOVERY RECTIFIER

Technical Data Data Sheet N0449, Rev. -

Features

- Glass Passivated Die Construction
- High current capability
- Low Forward Voltage Drop, High Efficiency
- Low Power Loss
- Fast Recovery Time
- High Surge Current Capability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Data

- Case: Molded Plastic
- Epoxy: UL 94V-0 rate flame retardant
- Polarity: Cathode Band or Cathode Notch
- Marking: Type Number
- Mounting Position: Any
- High temperature soldering guaranteed: 250°C/10 seconds/.375" ,(9.5mm) lead

Marking Diagram:



DO-201AD							
Dim	Min	Max	Min	Max			
Α	25.4		1.000	Ι			
В	8.50	9.50	0.335	0.374			
с	1.20	1.30	0.047	0.051			
D	5.0	5.60	0.197	0.220			
Ali	In mm		In inch				

Where XXXXX is YYWWL

FR301G	= Part Name
SSG	= SSG
ΥY	= Year
WW	= Week
L	= Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

Ordering Information

Device	Package	Shipping		
FR301G-FR307G	DO-201AD (Pb-Free)	1250pcs / tape		

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

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Maximum Ratings and Electrical Characteristics @TA=25° C unless otherwise specified

Characteristic	Symbol	FR 301G	FR 302G	FR 303G	FR 304G	FR 305G	FR 306G	FR 307G	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	Vrrm Vrwm Vr	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	VR(RMS)	35	70	140	280	420	560	700	V
Average Rectified Output Current @TL = 75°C	a	3.0					А		
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	125					А		
Forward Voltage @l= = 3.0A	Vfm	1.3					V		
Peak Reverse Current @T _A = 25° C At Rated DC Blocking Voltage @T _A = 125° C	IRм	5.0 100				μΑ			
Reverse Recovery Time (Note 1)	trr	150			250	250 500		nS	
Typical Junction Capacitance (Note 2)	q	60					pF		
Operating and Storage Temperature Range	Tj, Tstg	-65 to +150					°C		

Note: 1. Measured with $l_F = 0.5A$, $l_R = 1.0A$, $l_T = 0.25A$,

2. Measured at 1.0 MHz and applied reverse voltage of 4.0 V DC.



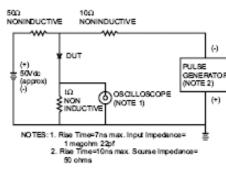
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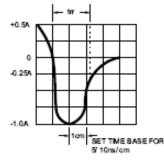
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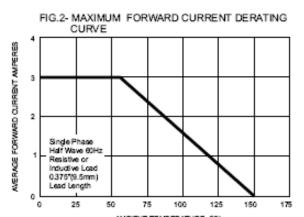
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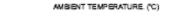
RATINGS AND CHARACTERISTIC CURVES (FR301G THRU FR307G)

FIG.1- REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM











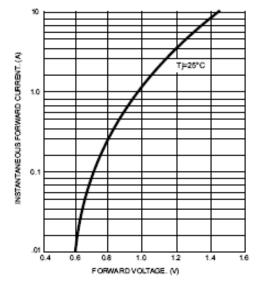
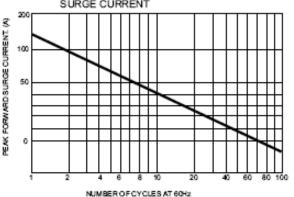
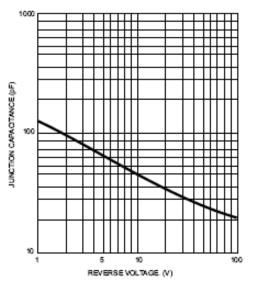


FIG.3- MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT







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